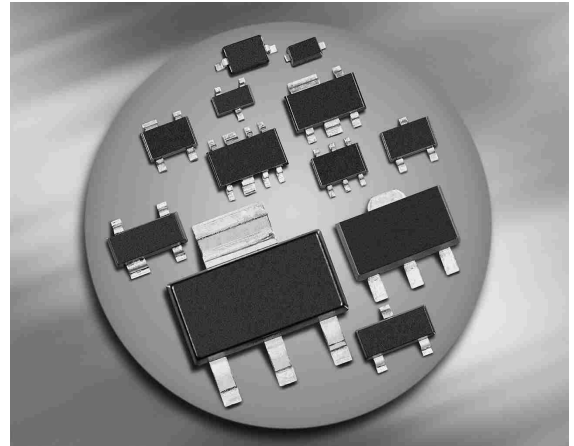
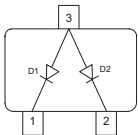


Silicon Low Leakage Diode

- Low-leakage applications
- Medium speed switching times
- Common anode configuration



BAW156



Type	Package	Configuration	Marking
BAW156	SOT23	common anode	JZs

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Peak reverse voltage	V_{RM}	85	
Forward current	I_F	200	mA
Surge forward current, $t = 1 \mu\text{s}$	I_{FS}	4.5	A
Total power dissipation $T_s \leq 35^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

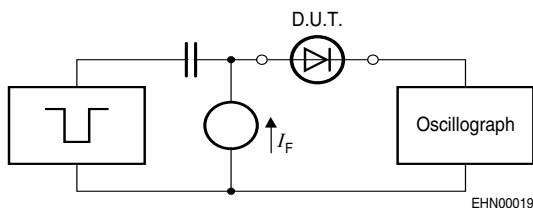
Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BAW156	R_{thJS}	≤ 460	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_{(BR)} = 100 \mu A$	$V_{(BR)}$	85	-	-	V
Reverse current $V_R = 75 V$ $V_R = 75 V, T_A = 150 ^\circ C$	I_R	- -	- -	5 80	nA
Forward voltage $I_F = 1 mA$ $I_F = 10 mA$ $I_F = 50 mA$ $I_F = 150 mA$	V_F	- - - -	- - - -	900 1000 1100 1250	mV
AC Characteristics					
Diode capacitance $V_R = 0 V, f = 1 MHz$	C_T	-	2	-	pF
Reverse recovery time $I_F = 10 mA, I_R = 10 mA$, measured at $I_R = 1 mA$, $R_L = 100 \Omega$	t_{rr}	-	0.6	1.5	μs

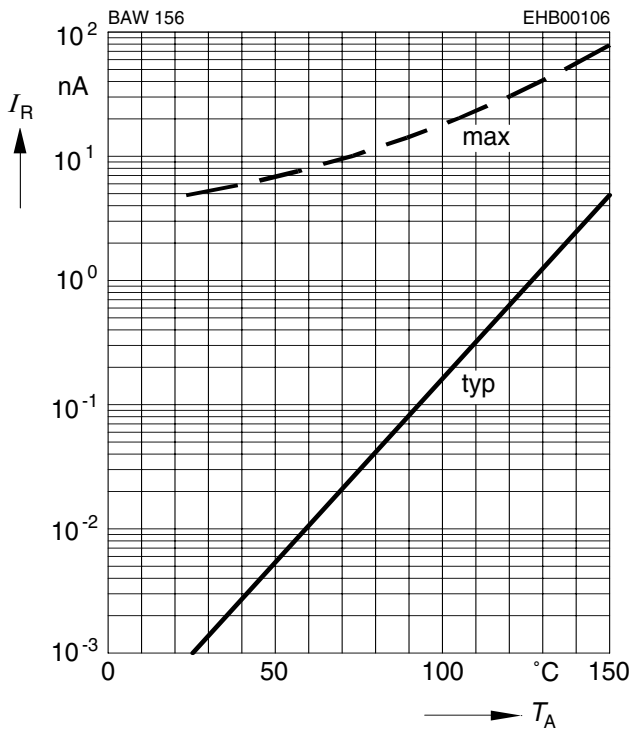
Test circuit for reverse recovery time


Pulse generator: $t_p = 10 \mu\text{s}$, $D = 0.05$, $t_r = 0.6 \text{ ns}$,
 $R_i = 50 \Omega$

Oscilloscope: $R = 50 \Omega$, $t_r = 0.35 \text{ ns}$, $C \leq 1 \text{ pF}$

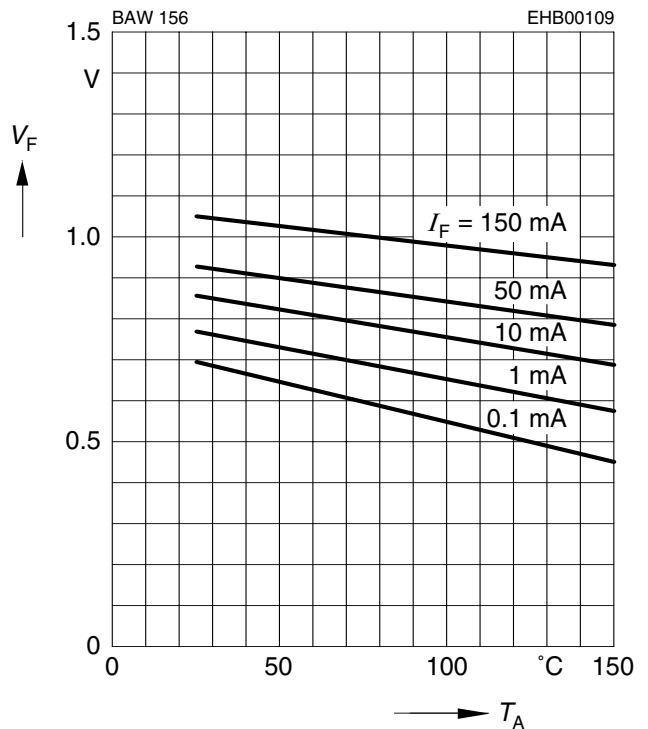
Reverse current $I_R = f(T_A)$

$V_R = 70V$



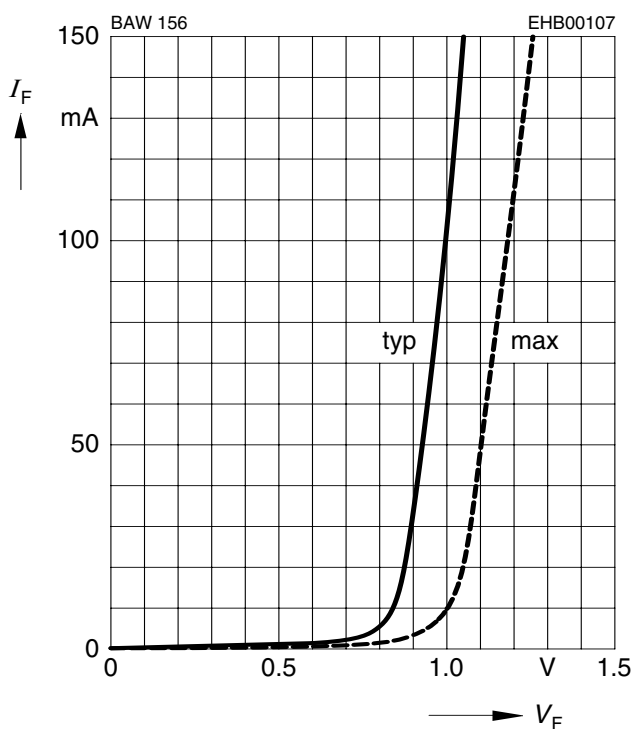
Forward Voltage $V_F = f(T_A)$

$I_F = \text{Parameter}$



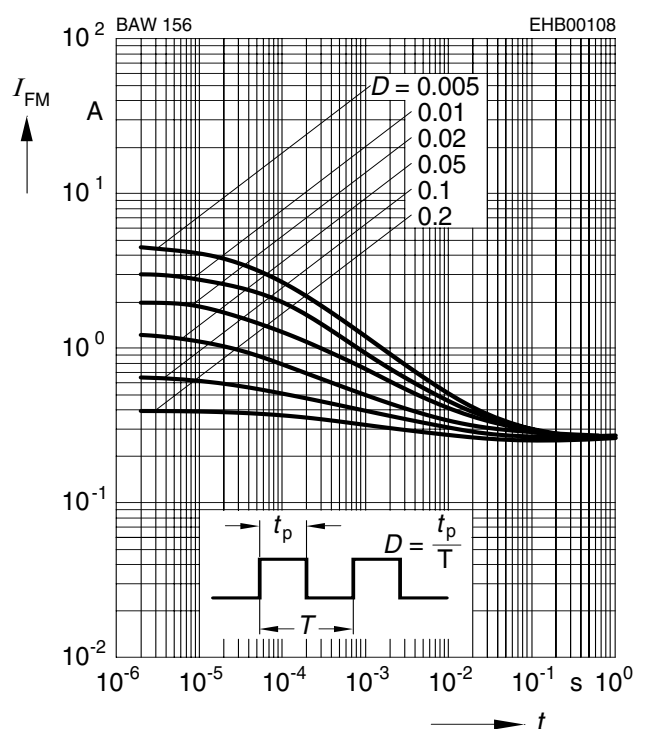
Forward current $I_F = f(V_F)$

$T_A = 25^\circ\text{C}$



Peak forward current $I_{FM} = f(t_p)$

$T_A = 25^\circ\text{C}$



Forward current $I_F = f(T_S)$

BAW156

